

IN THE CLAIMS

1. (Currently Amended) A bottom-gate thin-film transistor comprising:
a gate electrode, a gate insulating film, an active layer, and a protective insulating film deposited in that order on a substrate; and
a plurality of layers formed over said protective film with at least one electrode extending therethrough that is operatively and electrically connected to one of said active layer, an LDD region and a source-drain region;
wherein the protective insulating film has a thickness of less than 100 nm ~~or less~~, and the protective insulating film is formed on any one of the active layer, LDD region, and source-drain region, and
wherein there is no etched mask structure within the thin film transistor structure.
2. (Original) A bottom-gate thin-film transistor according to Claim 1, wherein the active layer comprises a polysilicon film.
3. (Currently Amended) A bottom-gate thin-film transistor according to either Claim 1 or 2, wherein the protective insulating film has a thickness of between about 5 ~~to and about~~ 50 nm.
- 4-9. (Canceled)
10. (Withdrawn) A liquid crystal display device comprising:
a TFT substrate comprising an interlayer insulating film, a transparent electrode, and an alignment layer formed on a protective insulating film of a bottom-gate thin-film transistor according to any one of Claims 1 to 3;
a counter substrate provided with a counter electrode; and
a liquid crystal interposed between the TFT substrate and the counter substrate.
11. (Canceled)
12. (Withdrawn) An organic EL device comprising:
a bottom-gate thin-film transistor according to any one of Claims 1 to 3; and

an organic EL element driven by the bottom-gate thin-film transistor.

13. (Canceled)